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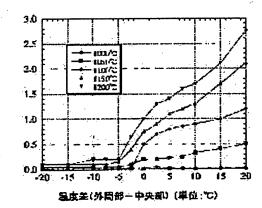
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(54) METHOD OF MANUFACTURING SEMICONDUCTOR WAFER

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method of manufacturing a semiconductor wafer, which employs a heat treatment for suppressing slip displacement even when heat treatment is conduced by a RTA equipment.

SOLUTION: The method of manufacturing a semiconductor wafer includes a process of heat—treating a semiconductor wafer at a prescribed temperature by the RTA equipment. The semiconductor wafer is heat—treated, at a temperature, at least a part of the semiconductor wafer, which is in contact with a support jig for supporting the semiconductor wafer controlled, is 3 to 20°C lower than that at the central part of the semiconductor wafer.



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